



# Surface and Nano Sciences Lab

([www.phys.sinica.edu.tw/~nano/](http://www.phys.sinica.edu.tw/~nano/))



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Surface dynamics, epitaxial growth, atom manipulation  
bio-imaging

Calculations and simulations

**FIM, SPM, TEM**

**Theoretic work**

**UHV TEM + STM**

**LT STM + magnet**

Size-, shape-, and site-specific properties of nanomaterials

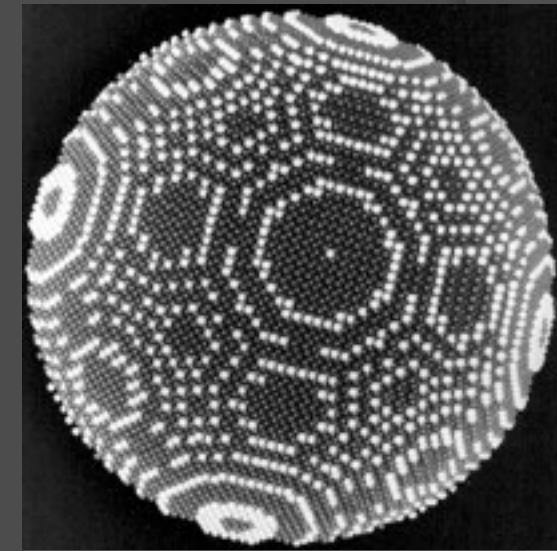
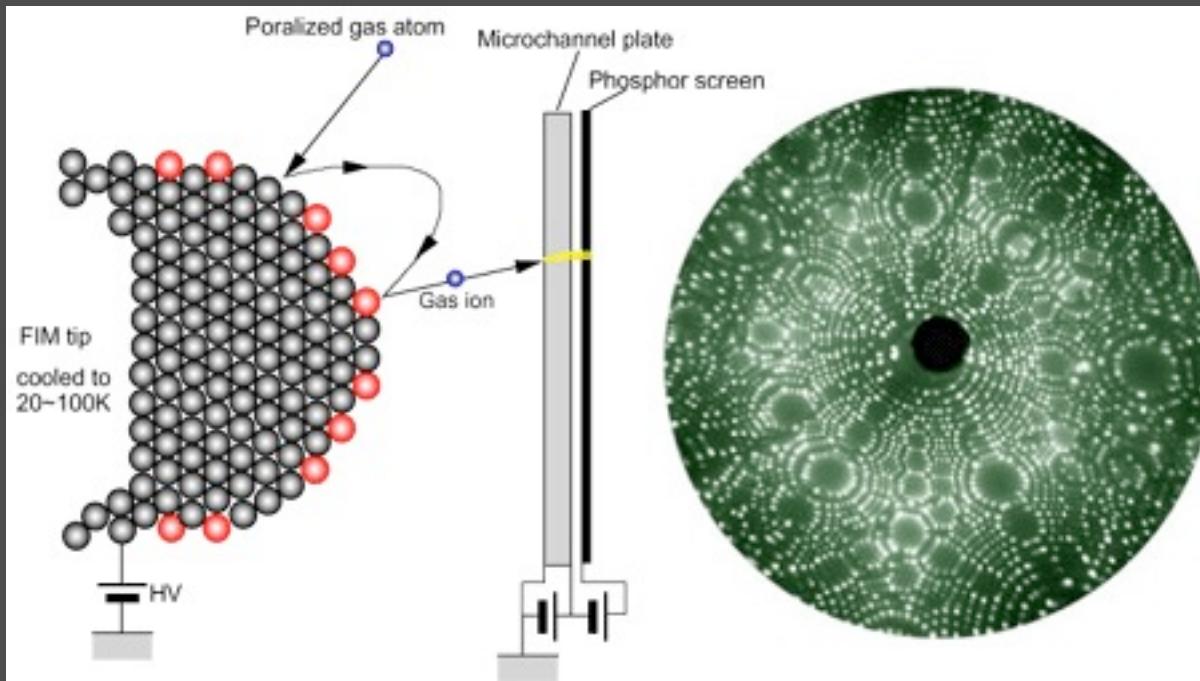
**Nanoscience**

Single spin detection,  
quantum phenomena  
in nanostructures

**Nanotechnology**

New tools, new instruments, new methods

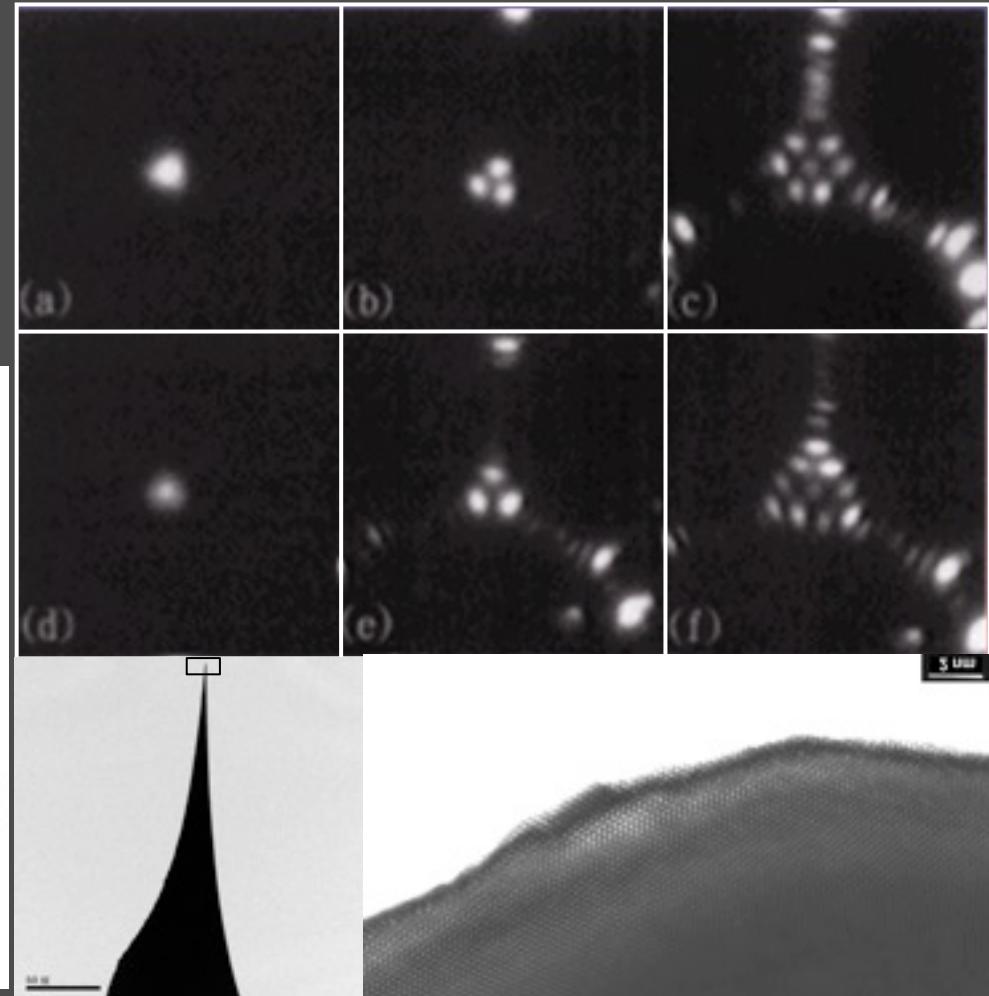
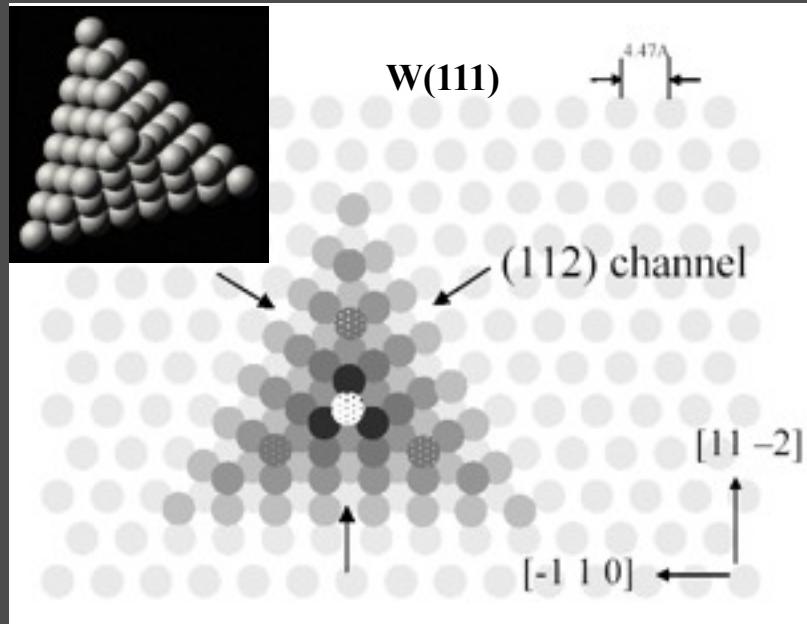
# Field Ion Microscopy



The image gas atoms in the vicinity of the specimen are polarized because of the high field and then attracted to the apex region of the specimen. After a series of collisions with the specimen during which the image gas atoms lose part of their kinetic energy, these image gas atoms become thermally accommodated to the cryogenic temperature of the specimen. If the field is sufficiently high, these image gas atoms are field ionized by a quantum-mechanical tunneling process. The ions produced are then radially repelled from the surface of the specimen towards the microchannel plate and screen assembly. A microchannel plate image intensifier positioned immediately in front of the phosphor screen produces between  $10^3$  and  $10^4$  electrons for each input ion. These electrons are accelerated towards the phosphor screen where they produce a visible image. The field-ion microscope was invented by Erwin Müller in 1951 at Pennsylvania State University.

# Single atom tip

- 1) STM probing
- 2) Coherent  $e^-$  beam
- 3) Point ion source



# E-beam and ion beam sources

Traditional

Ideal electron point source

Traditional

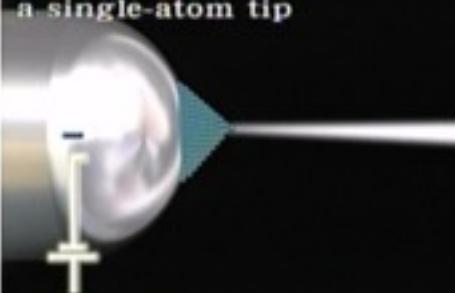
Ideal ion point source

The field emission electron source



Low brightness,  
High aberration,  
Poor coherence.

The electron source field emitted from a single-atom tip



High brightness,  
Small aberrations,  
High spatial coherence,  
Be focused very easily.

The field ion source



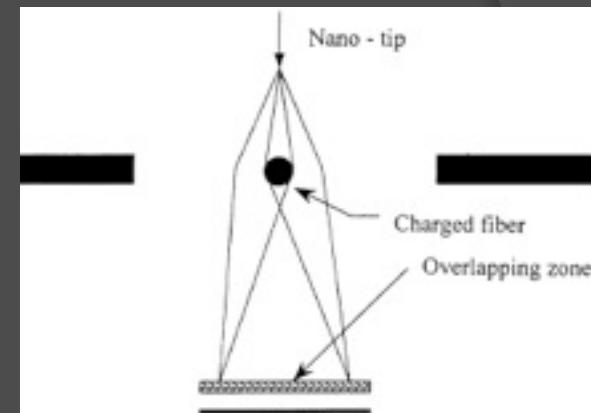
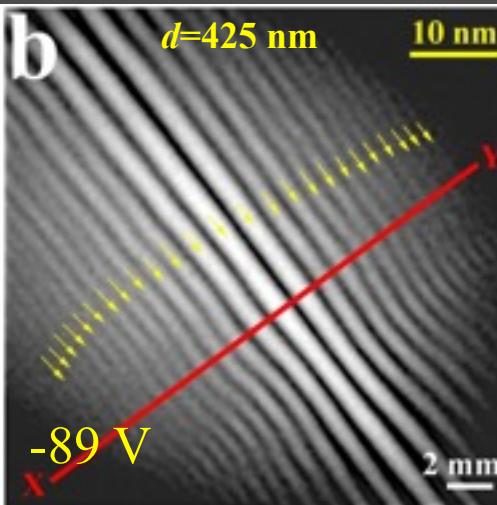
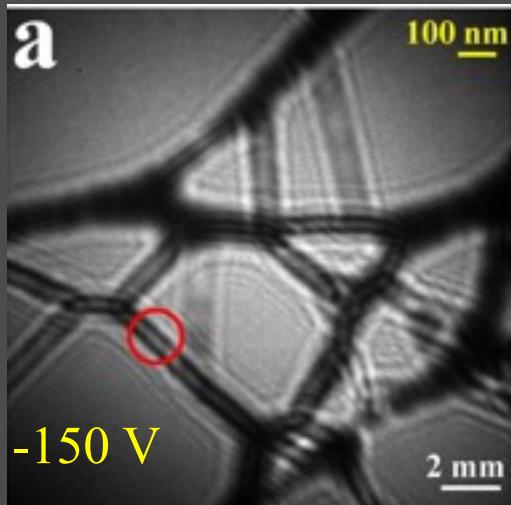
Low brightness,  
High aberration,  
Poor stability

The field ion source emitted from a single-atom tip



High brightness,  
Small aberrations,  
High stability,  
Be focused very easily.

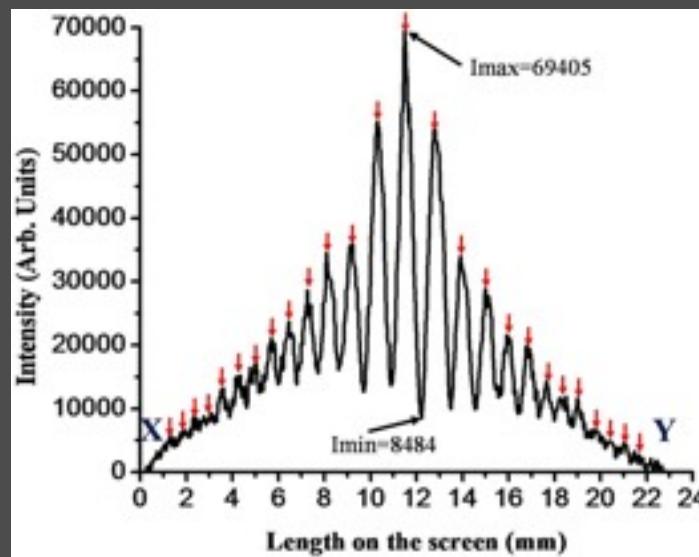
# High degree of spatial coherence



## Electron Biprism

Visibility

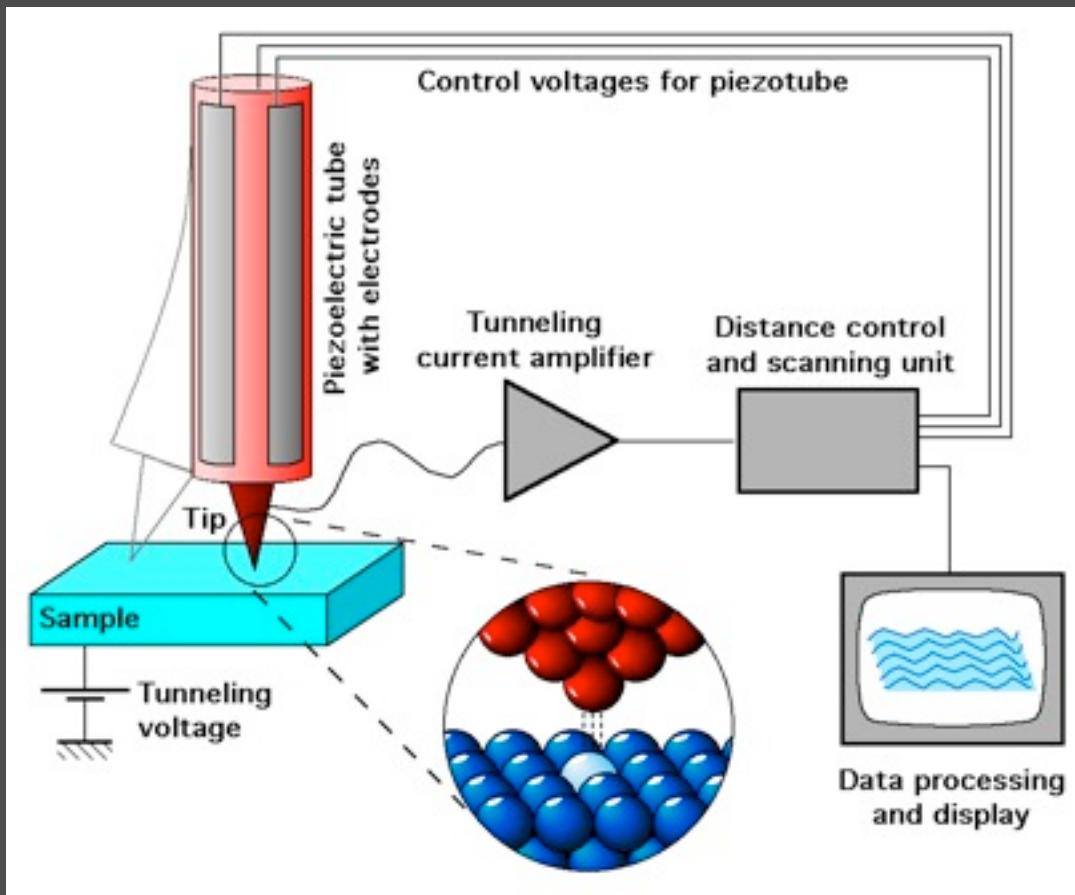
$$V = \frac{(I_{\max} - I_{\min})}{(I_{\max} + I_{\min})} = 0.78$$



SWNT bundle can act as a nanoprism, which splits the wavefront of an incoming electron wave into two coherent partial waves, which are deflected by the electric fields around the nanoprism in opposite directions and meet on the screen.



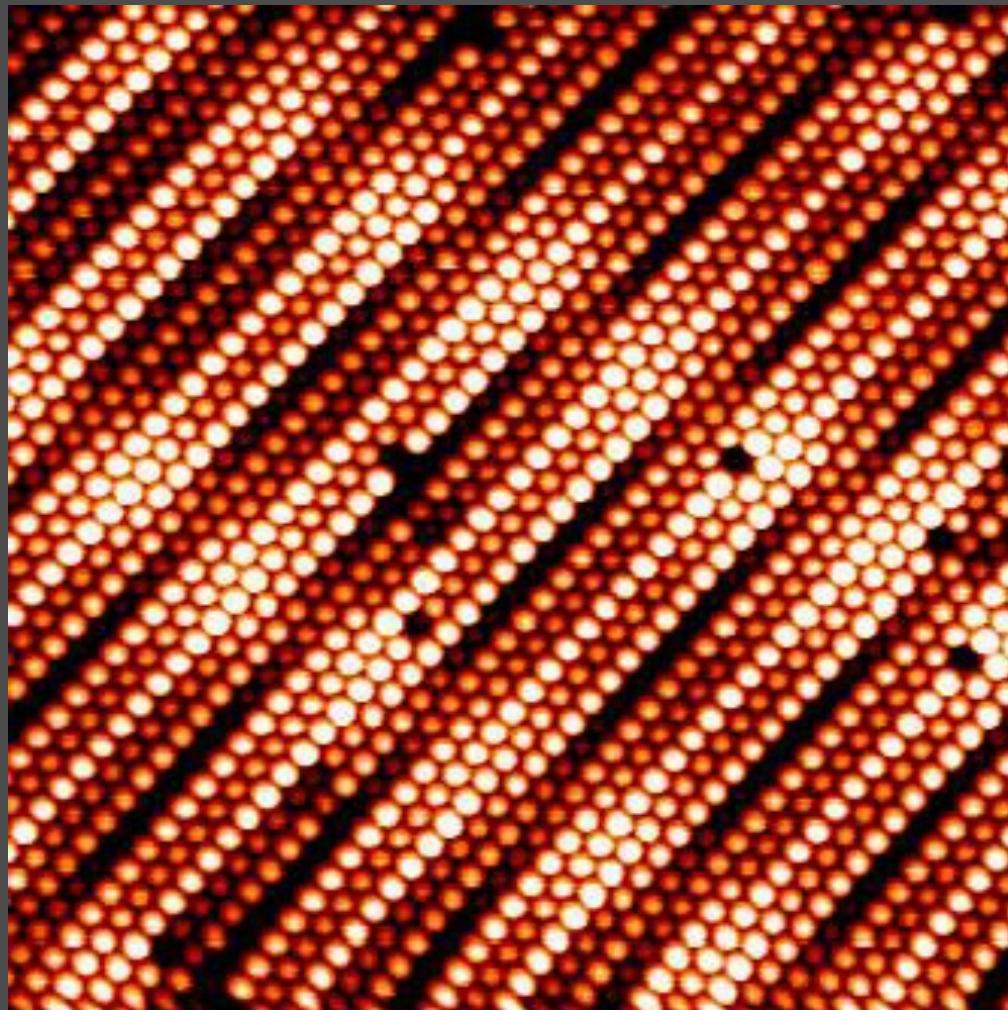
# Scanning Tunneling Microscopy



## References:

1. G. Binnig, H. Rohrer, C. Gerber, and Weibel, Phys. Rev. Lett. **49**, 57 (1982); and *ibid* **50**, 120 (1983).
2. J. Chen, *Introduction to Scanning Tunneling Microscopy*, New York, Oxford Univ. Press (1993).

# Pt(001) reconstructed Surface



Surface Science 306, 10 (1994)



# Surface and interface properties of ultrathin metal films on Si and Cu substrates

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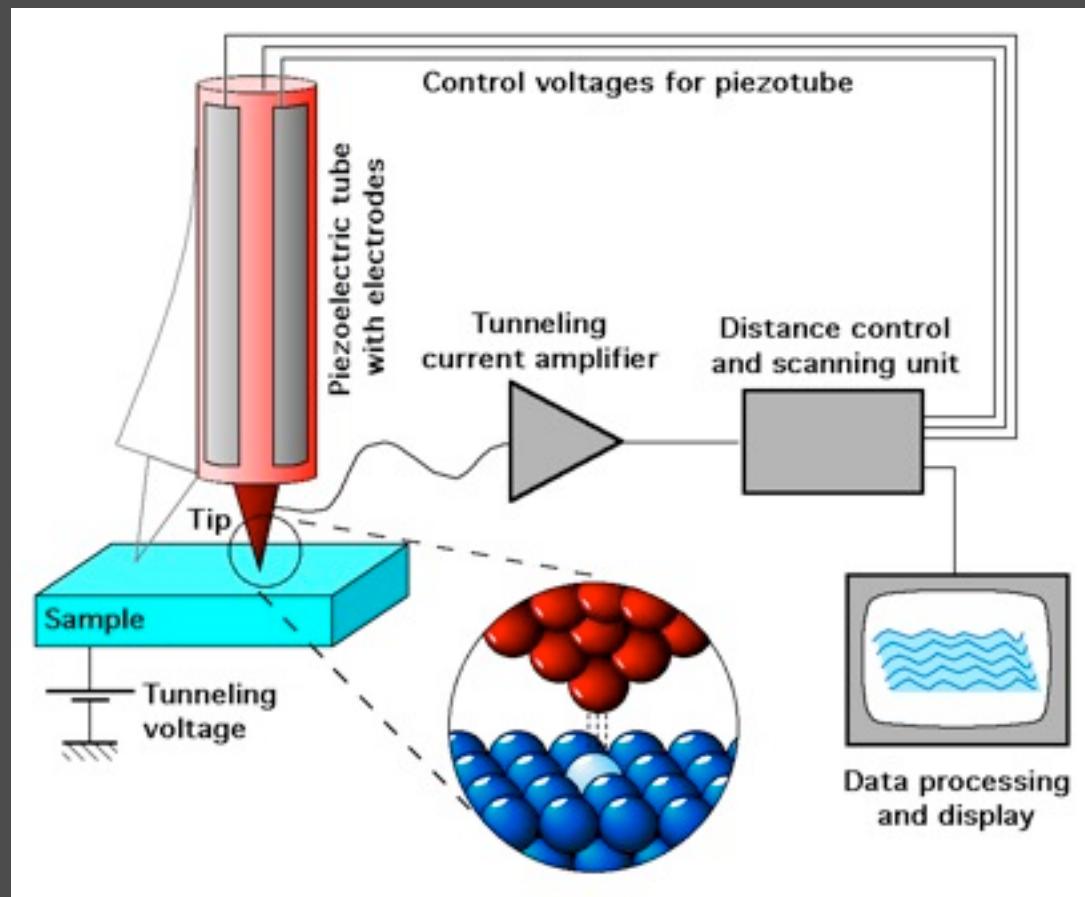
Supported by the National Program for  
Nanoscience and Technology, NSC, Taiwan



## Outline

- Quantum well states in ultrathin Pb films
  - Manifestation of interfacial potential
  - Effect of image potential
- Gundlach oscillations in STM configuration
  - Work function measurements
- Transmission resonance through thin films
  - Determination of film thickness

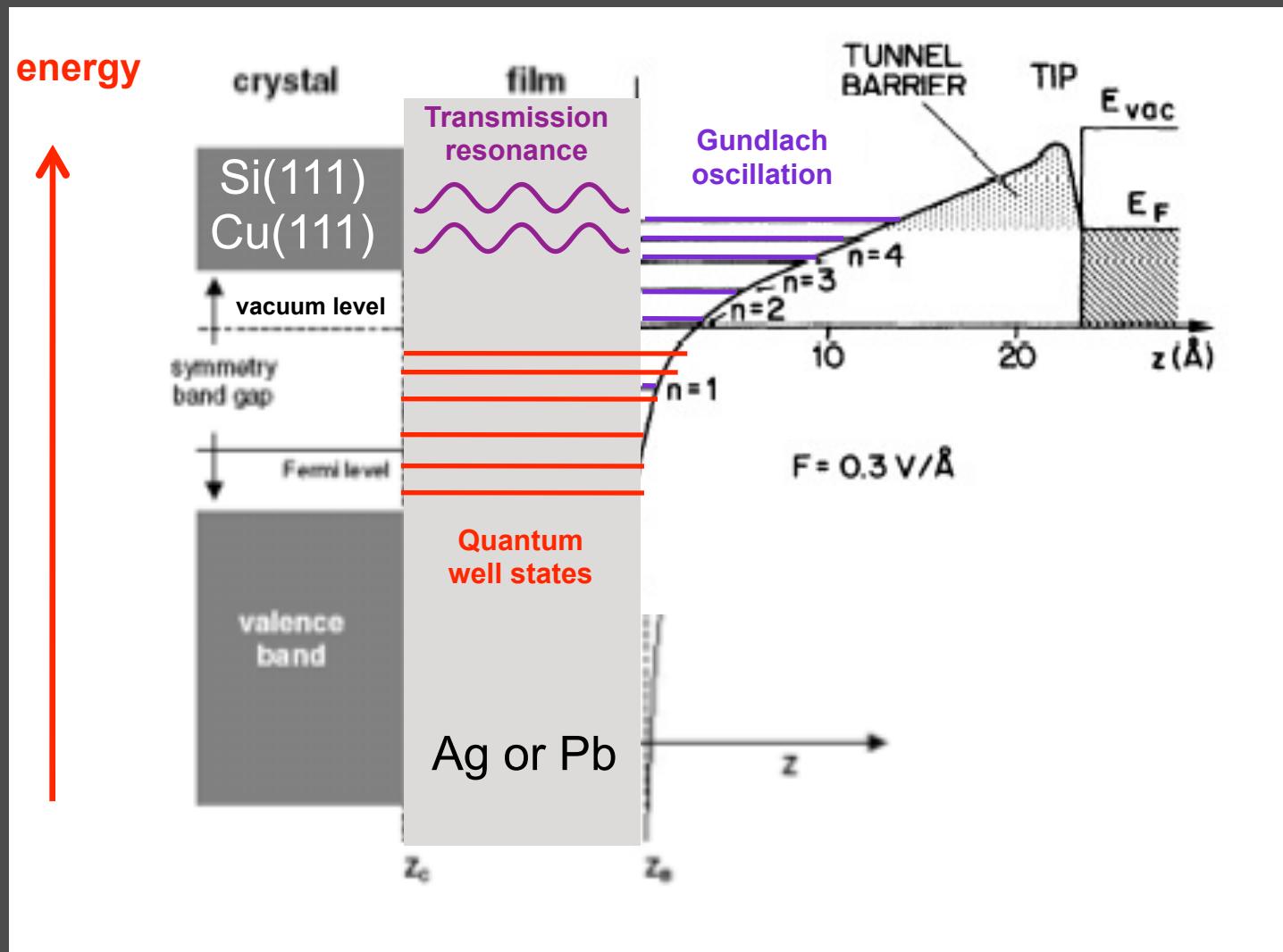
# Scanning Tunneling Microscopy



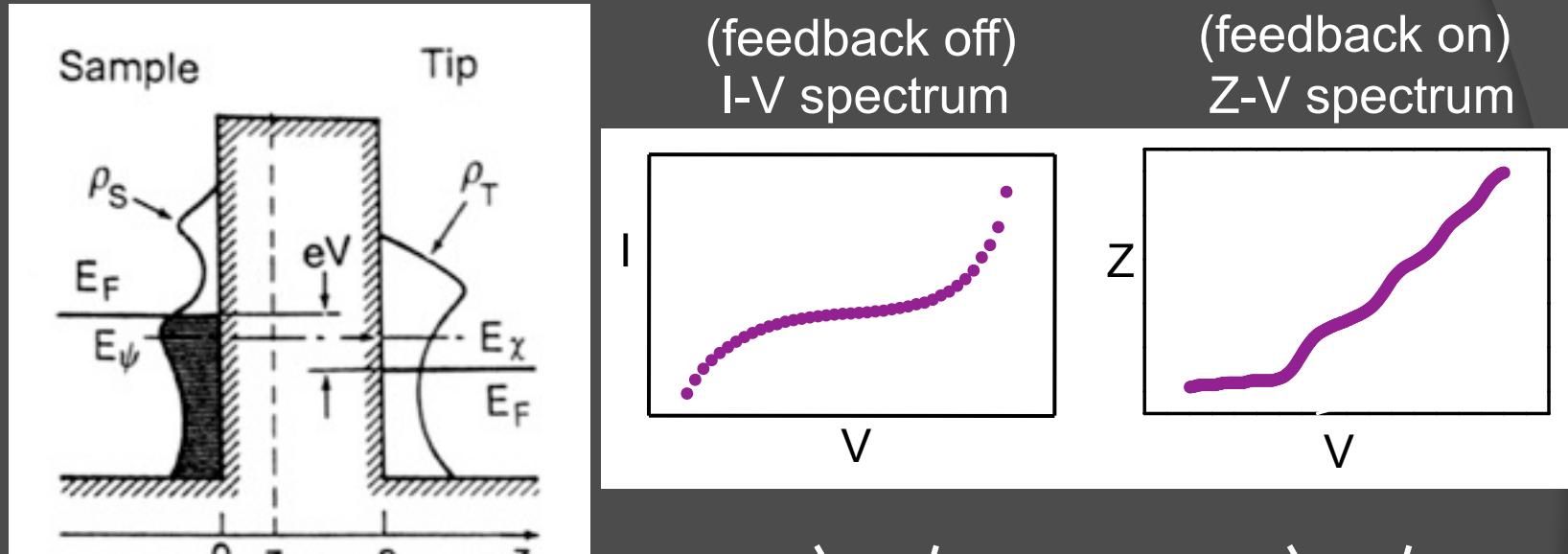
## References:

1. G. Binnig, H. Rohrer, C. Gerber, and Weibel, Phys. Rev. Lett. **49**, 57 (1982); and *ibid* **50**, 120 (1983).
2. J. Chen, *Introduction to Scanning Tunneling Microscopy*, New York, Oxford Univ. Press (1993).

# Various quantum phenomena



# Scanning Tunneling Spectroscopy

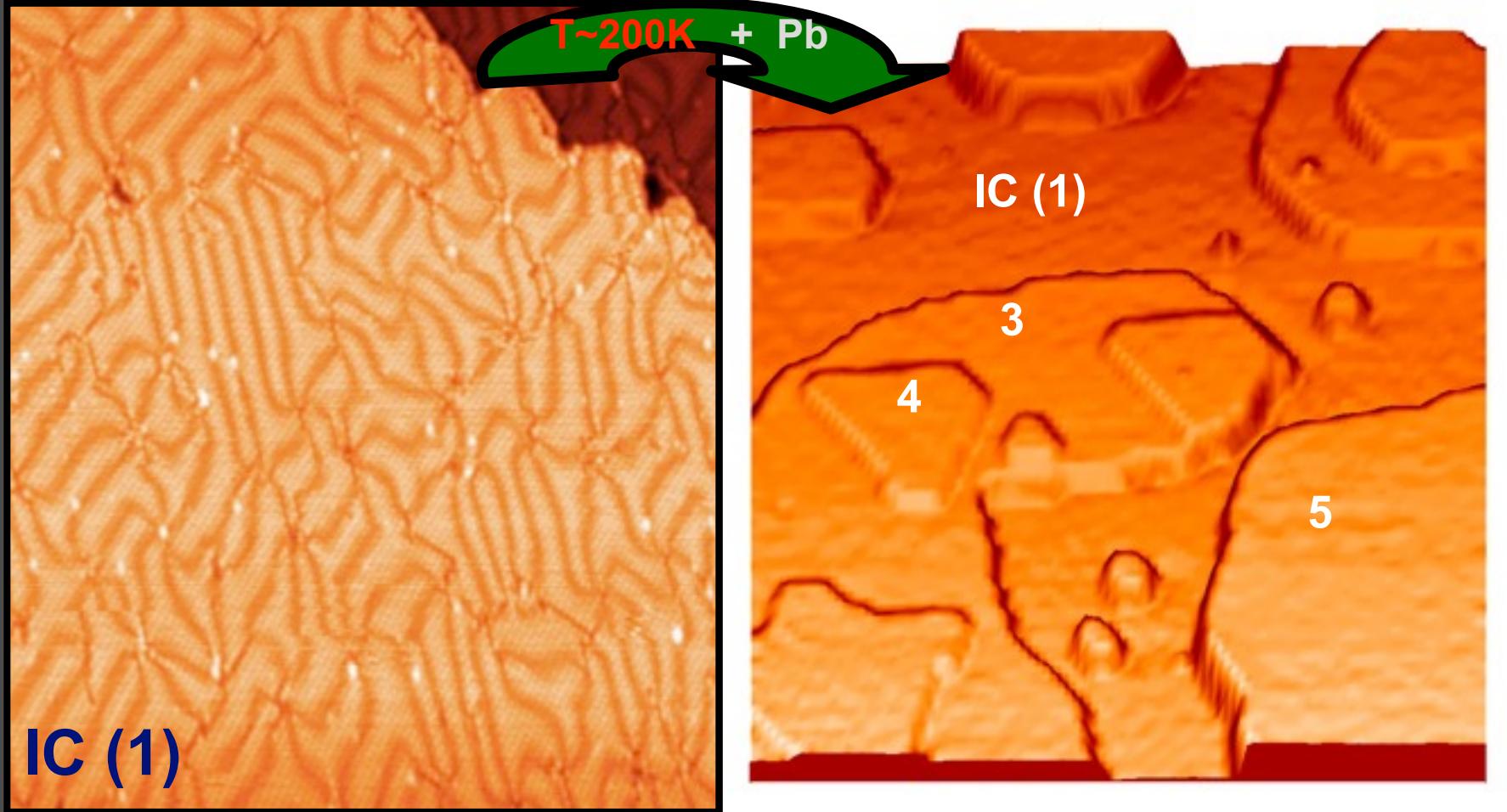


$$I \propto \int_0^{eV} \rho_s(E_F - eV + \varepsilon) \rho_T(E_F + \varepsilon) d\varepsilon$$

$$\rho_T \text{ is constant} \Rightarrow dI/dV \propto \rho_s(E_F - eV)$$

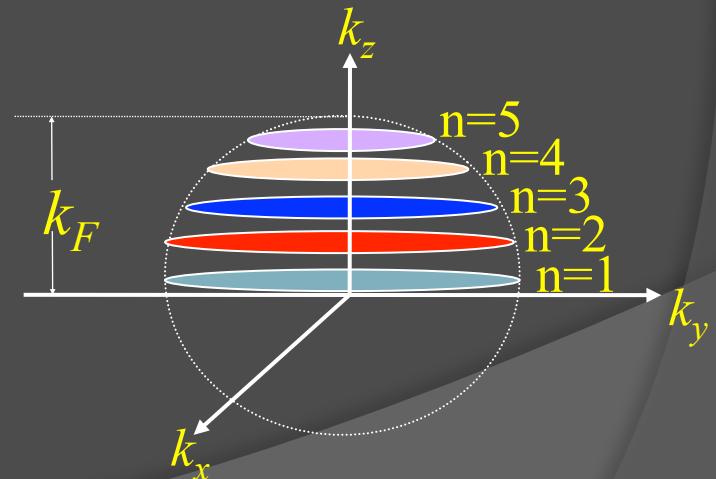
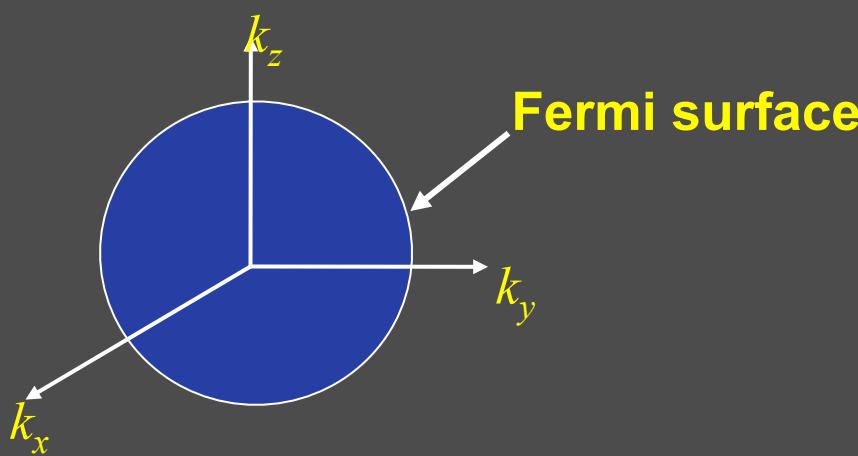
sample

## Pb islands on the IC Pb/Si(111)

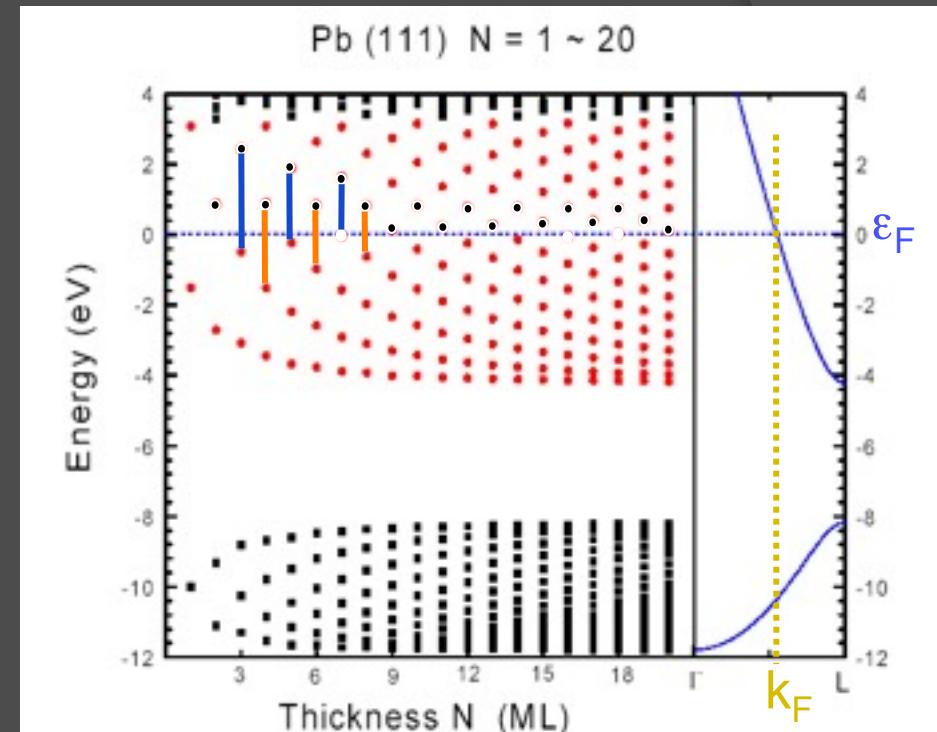
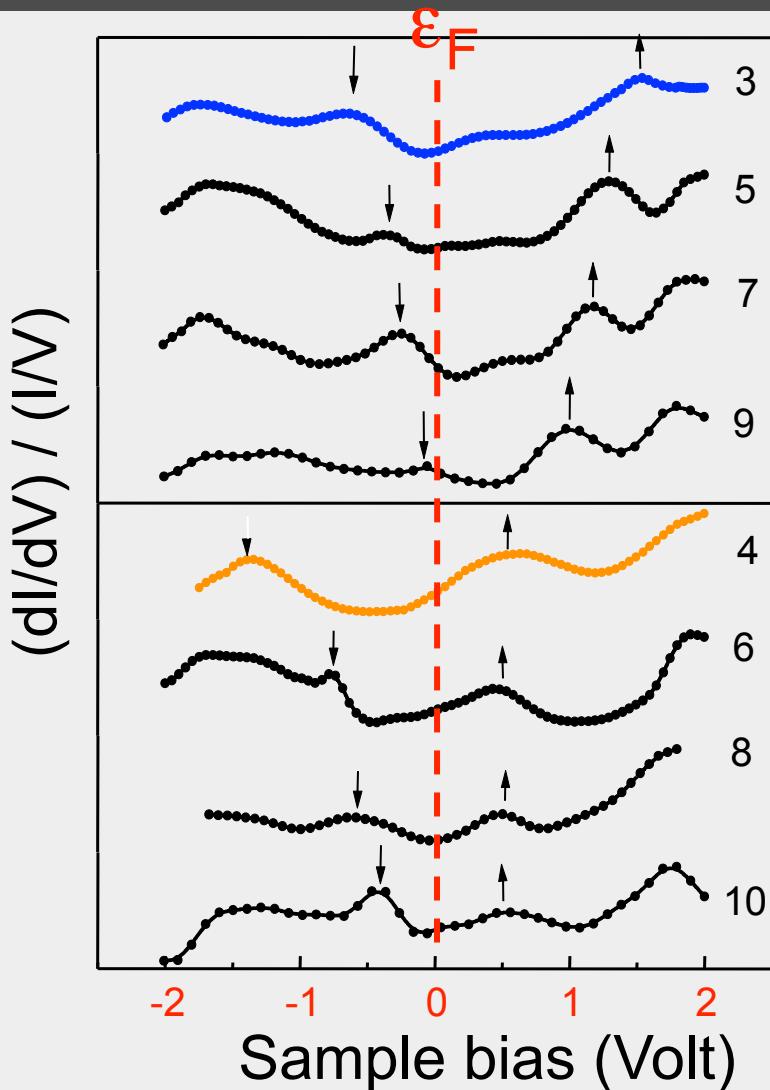


## Quantum size effect

$\lambda$  = de Broglie wavelength of electron  
 $a$  = thickness of metal film



# Spectra for Pb Films

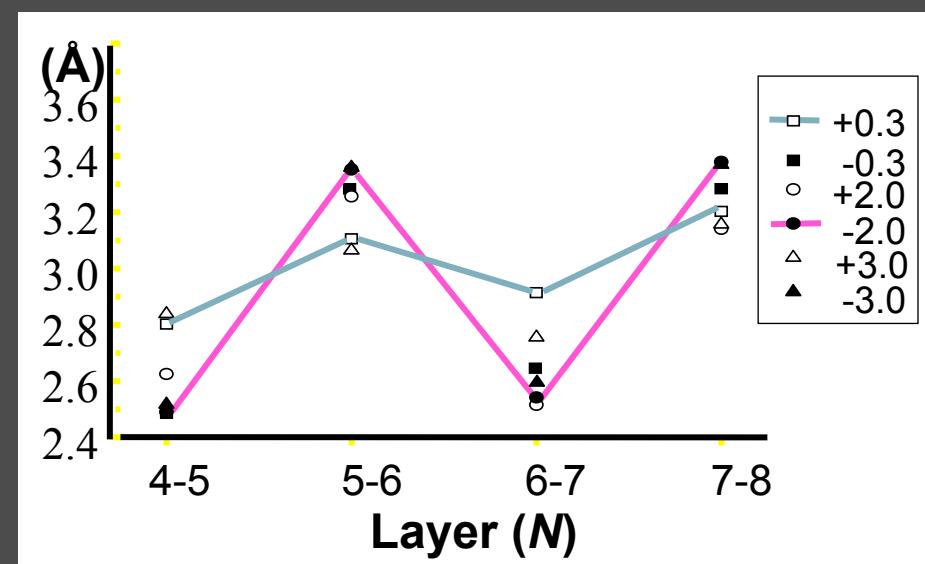
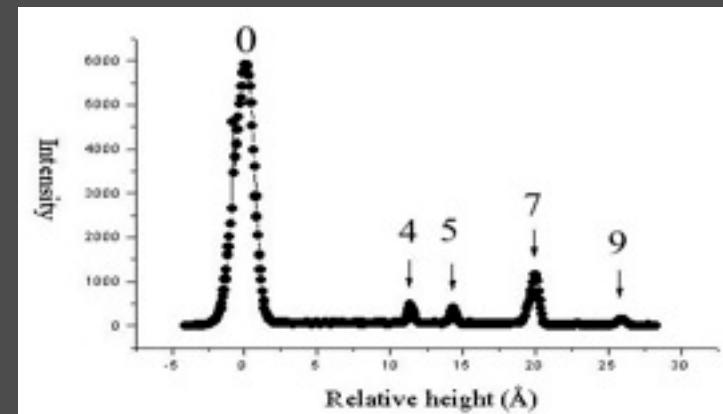
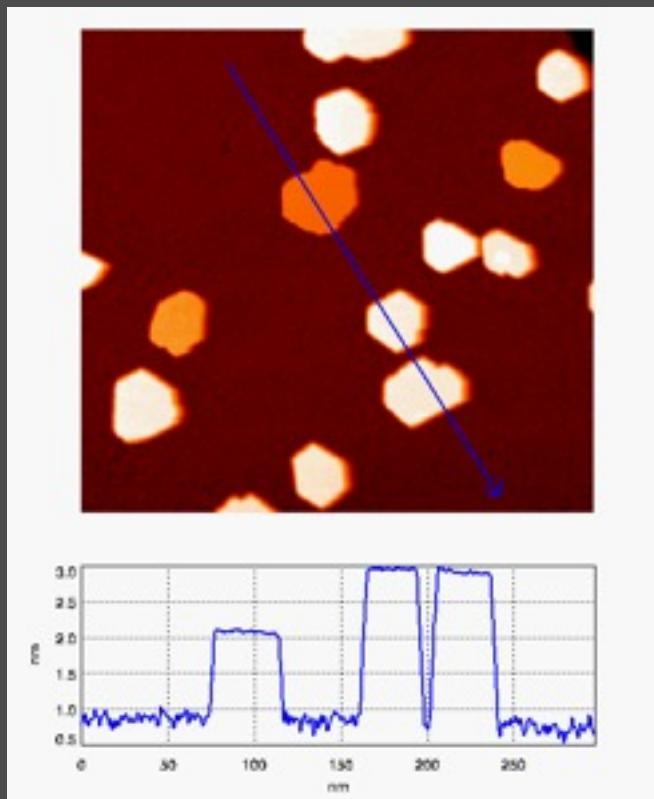


C.M. Wei and M.Y. Chou

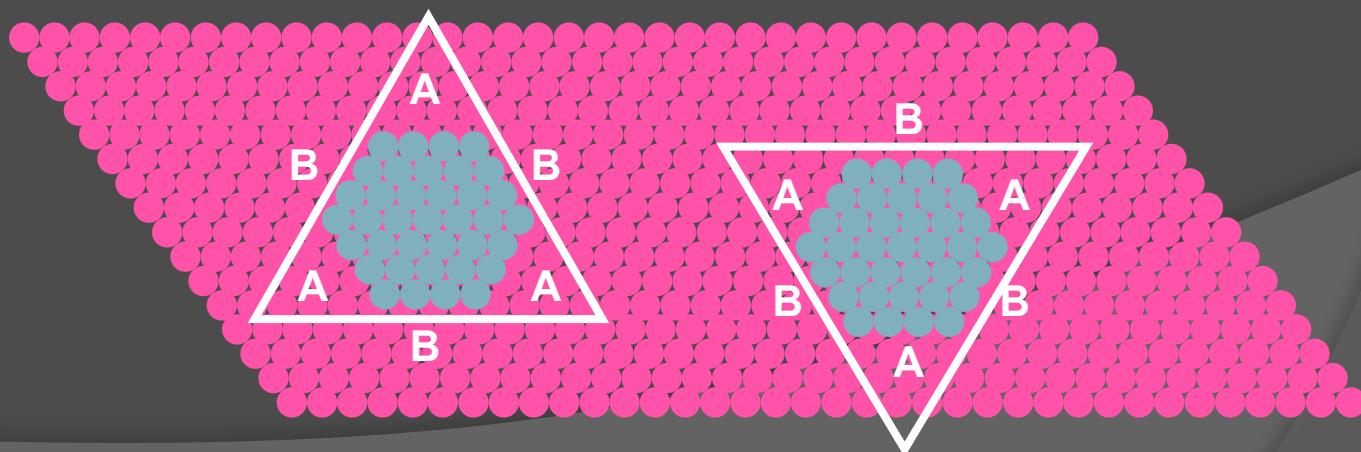
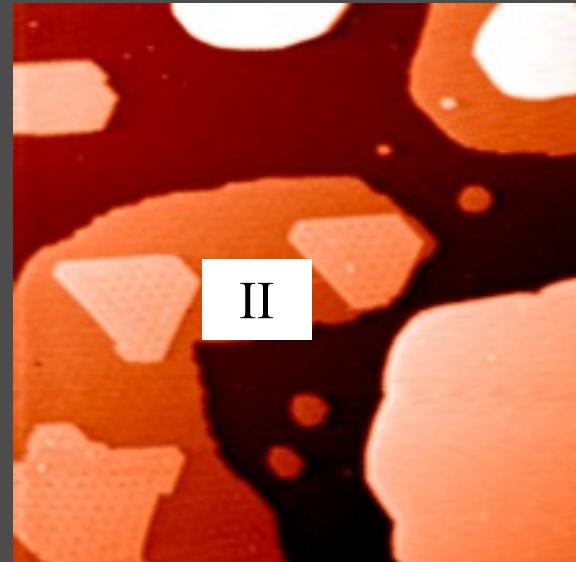
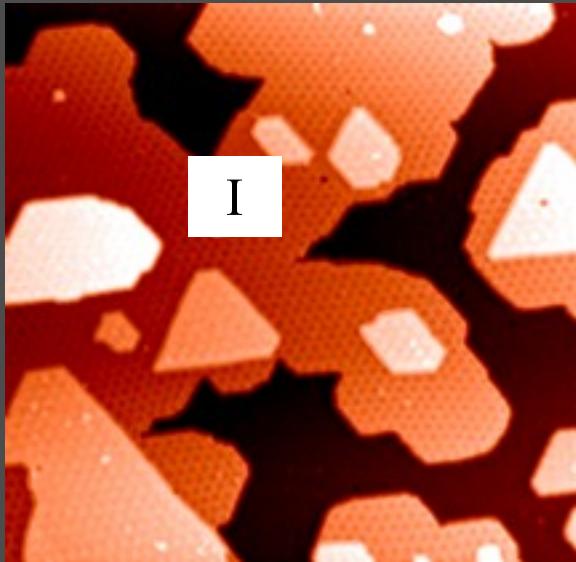
$$d_0 = 2.85 \text{ \AA} \quad \lambda_F = 3.94 \text{ \AA}$$

$$2d_0 \approx 3(\lambda_F/2)$$

# Apparent island heights

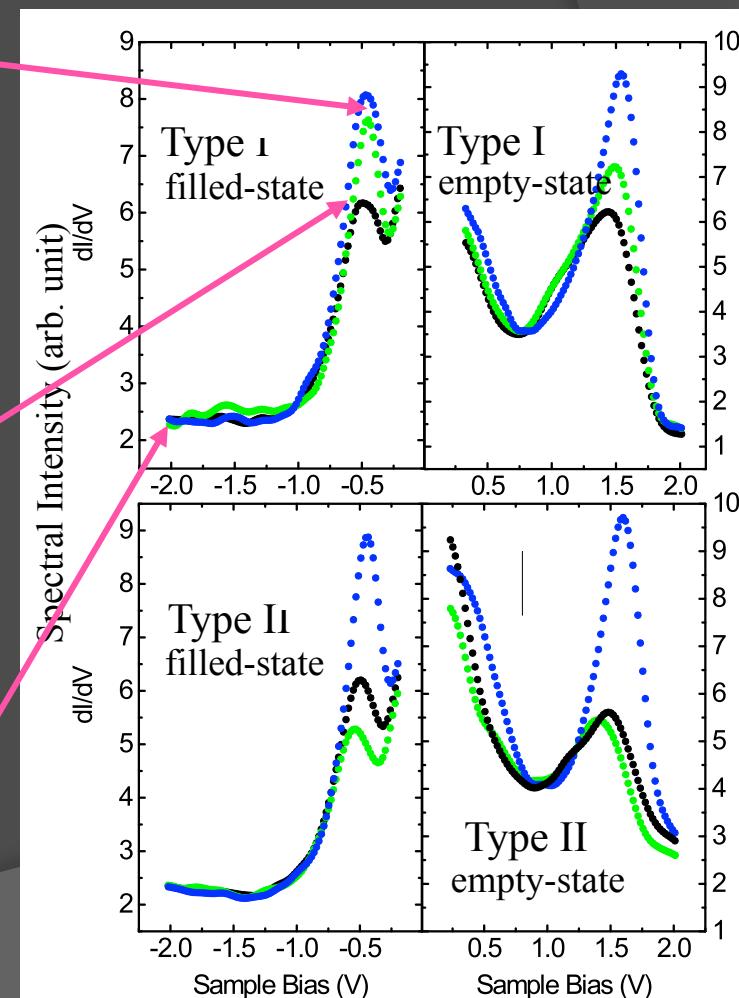
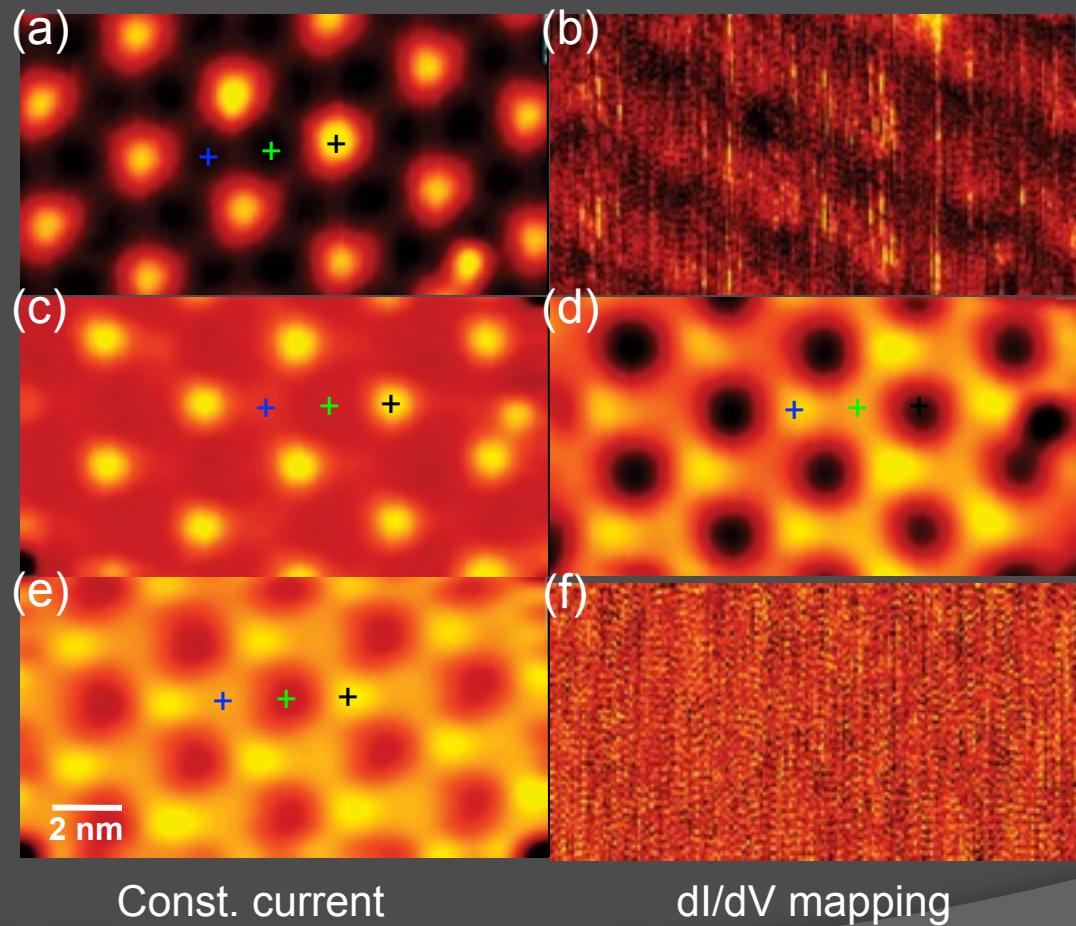


## Difference in layer stacking

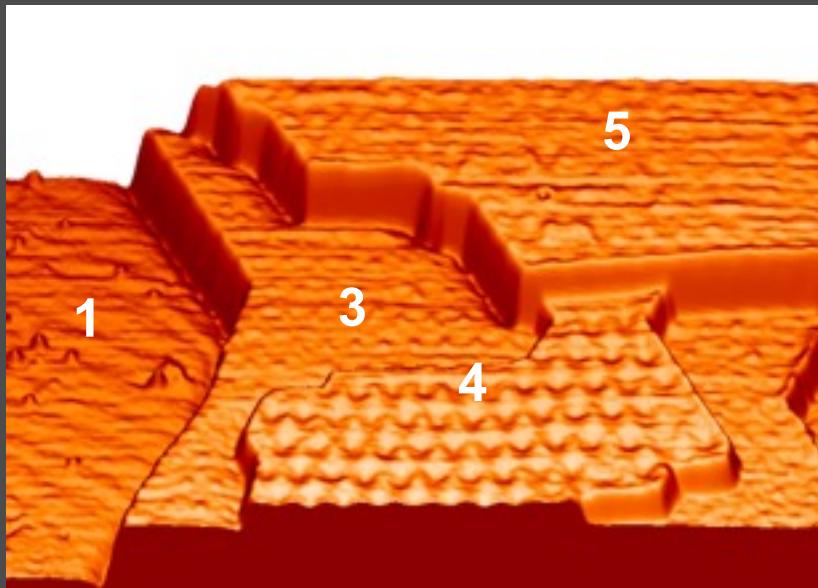


# Characteristics of Pb islands---

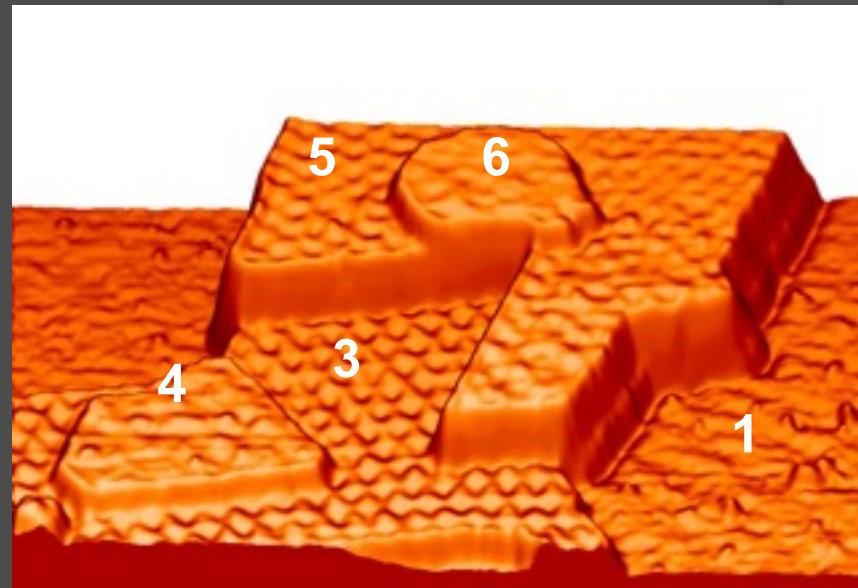
## Bias-dependent imaging contrast



# Characteristics of Pb island: oscillatory and complementary contrast



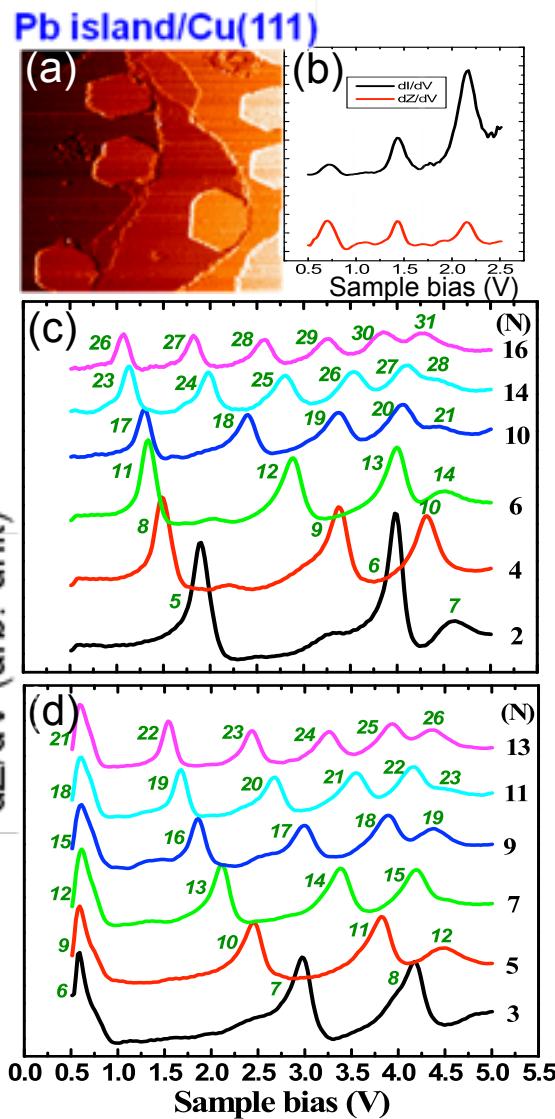
Type II



Type I

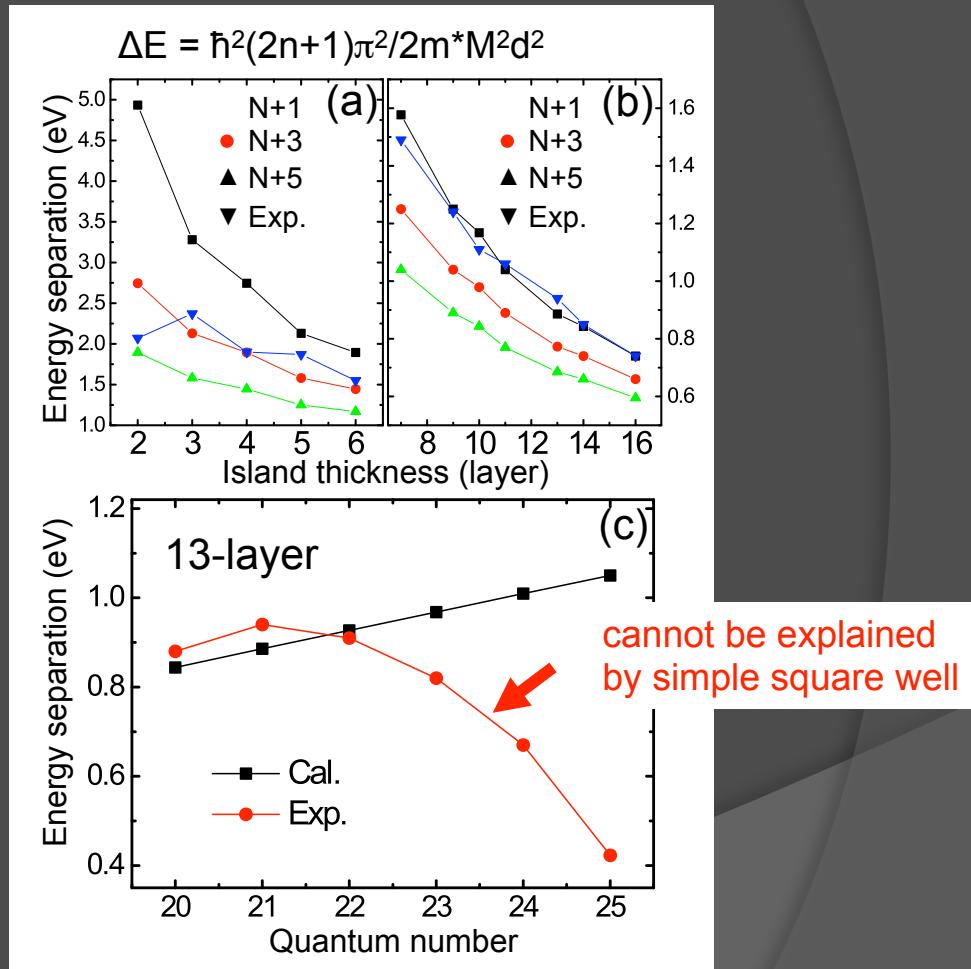
W.B. Jian *et al.*, Phys. Rev. Lett. **90**, 196603 (2003)

# Effect of image potential on quantum well states



even

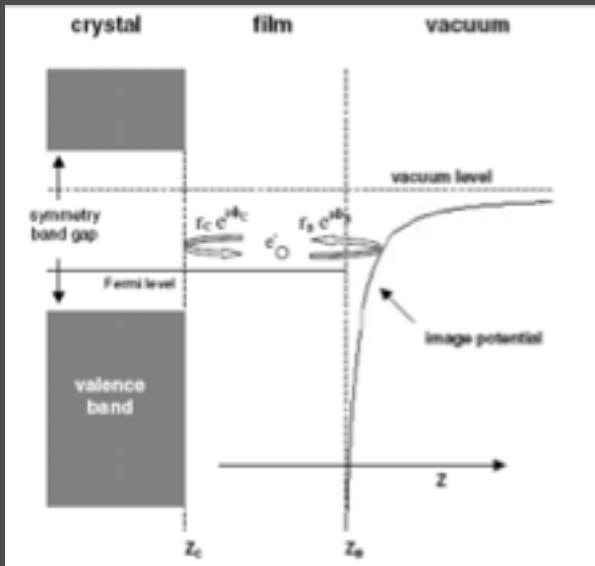
odd



Phys. Rev. Lett. 102, 196102 (2009)



# Phase contribution of image potential



Phase accumulation (PA) model: total phase= $2n\pi$   
For simple square well:

$$2k(N+1)d=2n\pi$$

Including phase  $\phi_B$  contributed from image potential

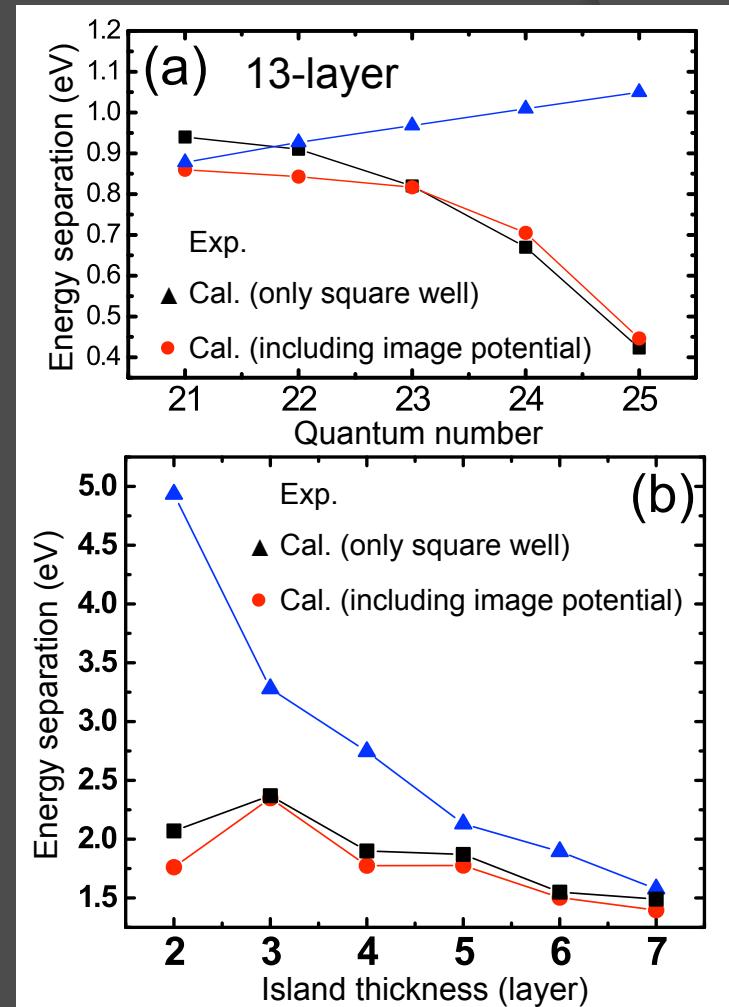
$$2k(N+1)d+\phi_B=2n\pi$$

and  $\phi_B/\pi=[3.4 \text{ eV}/(E_V-E)]^{1/2}-1$

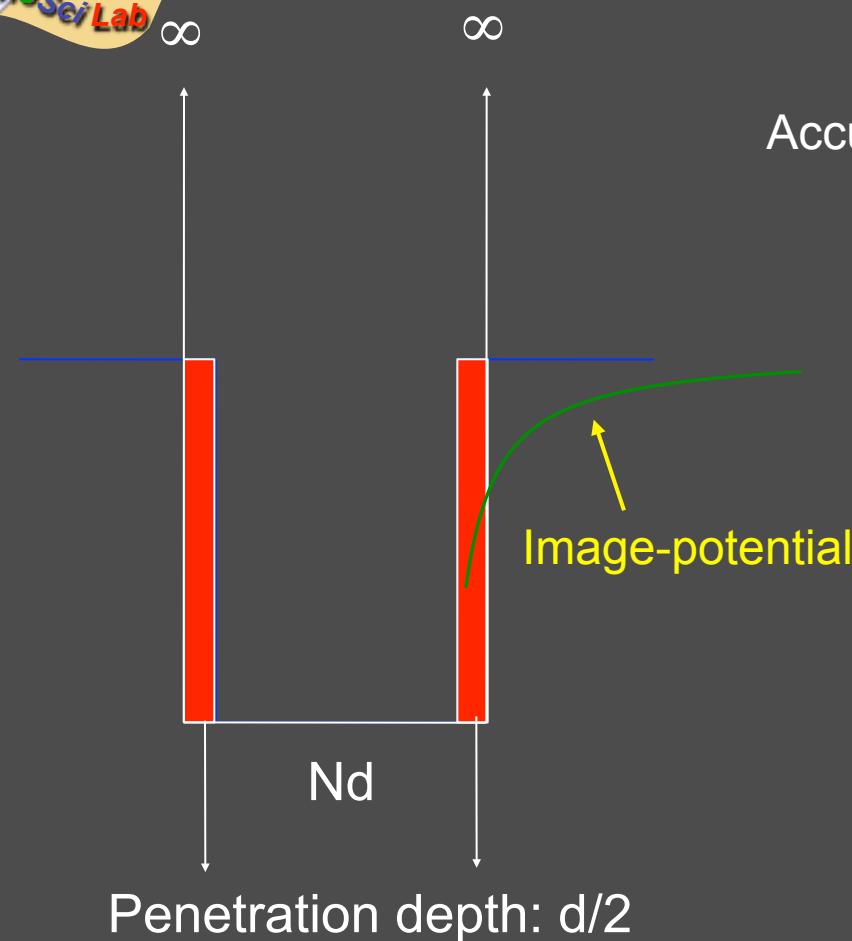
$E$ : energy of quantum well state

$E_V$ : Vacuum level

$$E_V=4.6 \text{ eV above } E_F$$

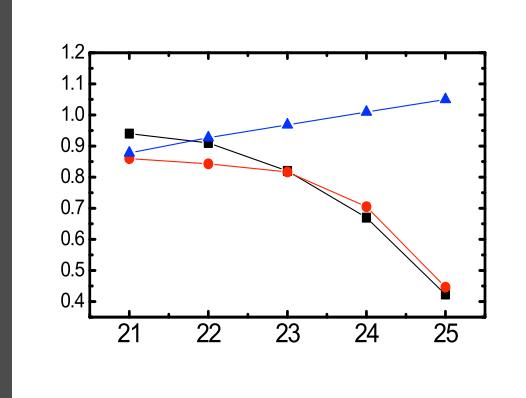


# Accumulative phase model



Accumulative phase for quantization:

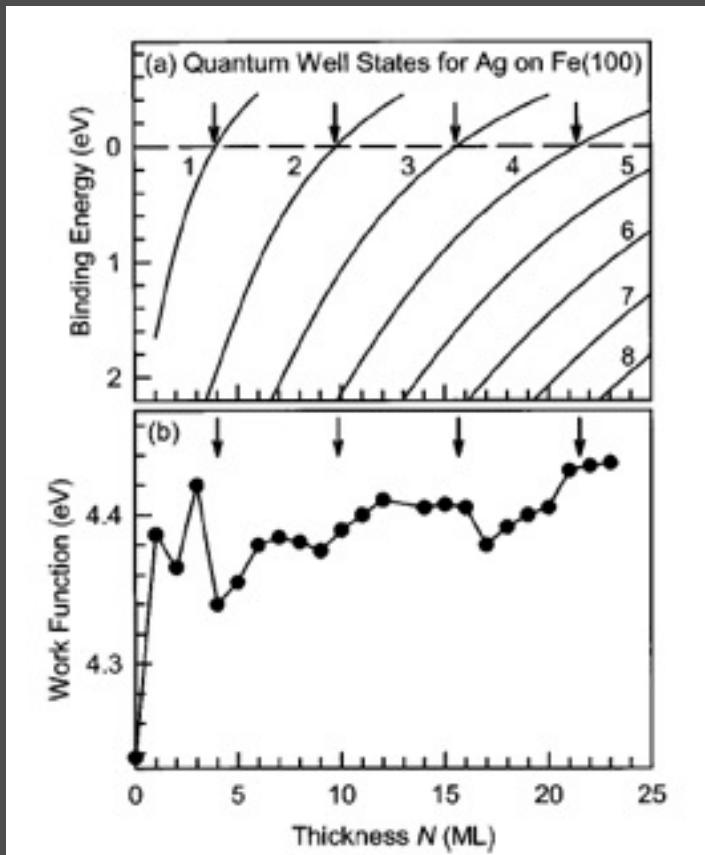
$$2k(N+1)d + \phi_B = 2n\pi$$



Finite square well with width  $Nd$  is approximated by infinite square well with width  $(N+1)d$  ( $M=N+1/2+1/2$ )

# Work function of ultrathin films

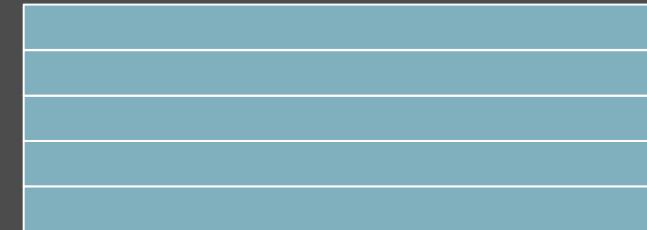
work function measurement for thin film  
using photo-emission spectroscopy



J. J. Paggel et al. 66, Phys. Rev. B  
(2002) 233403.

Broad beam technique

require layer by layer growth

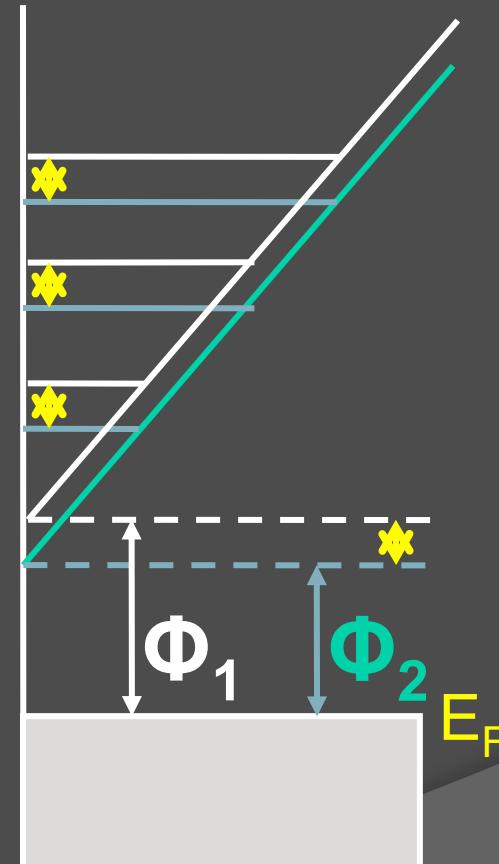
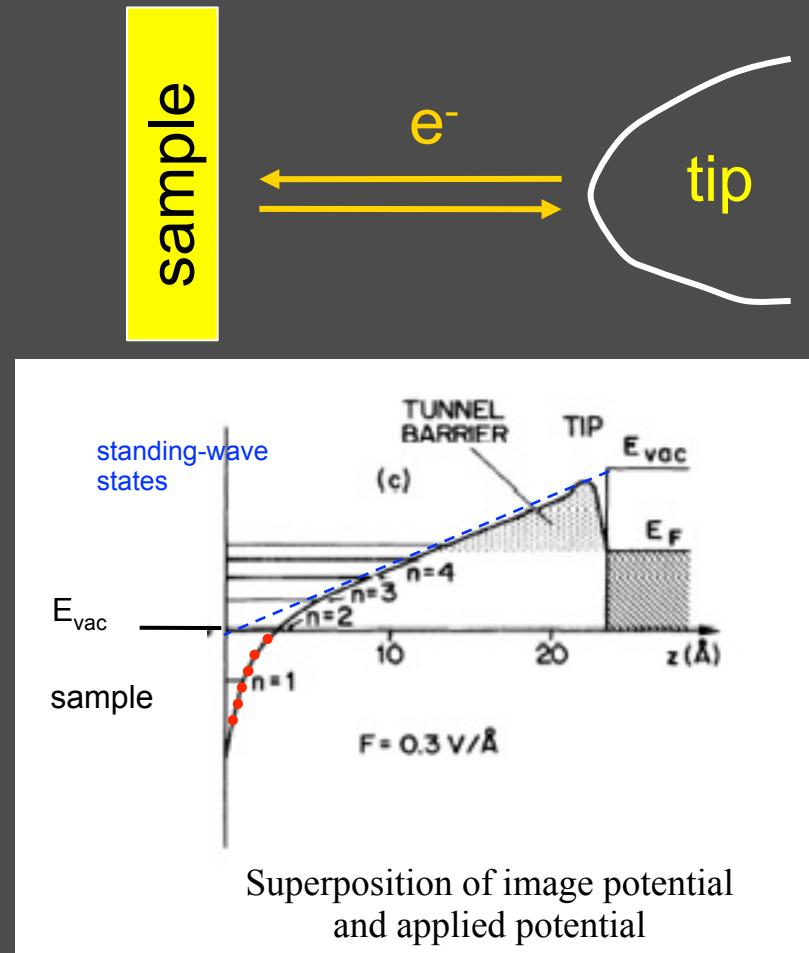


Average work function of various thickness



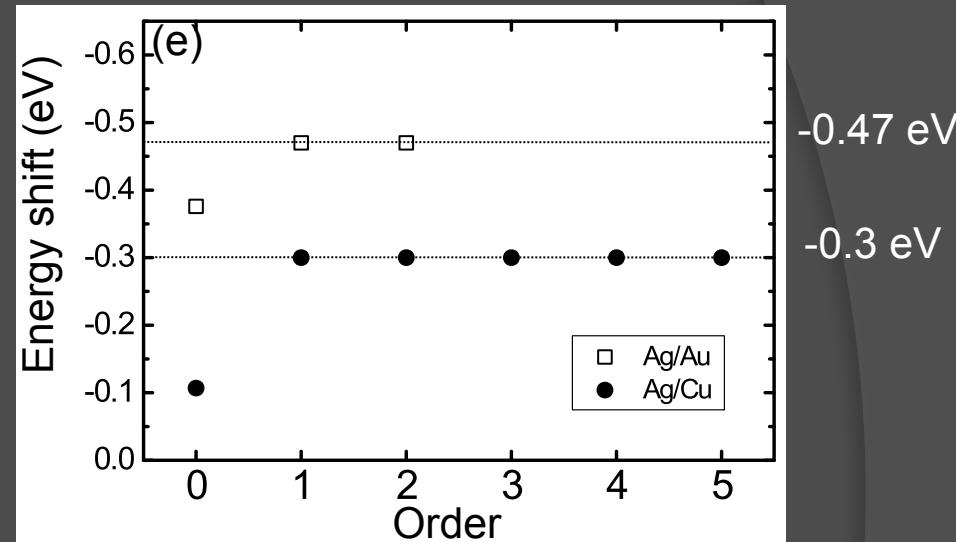
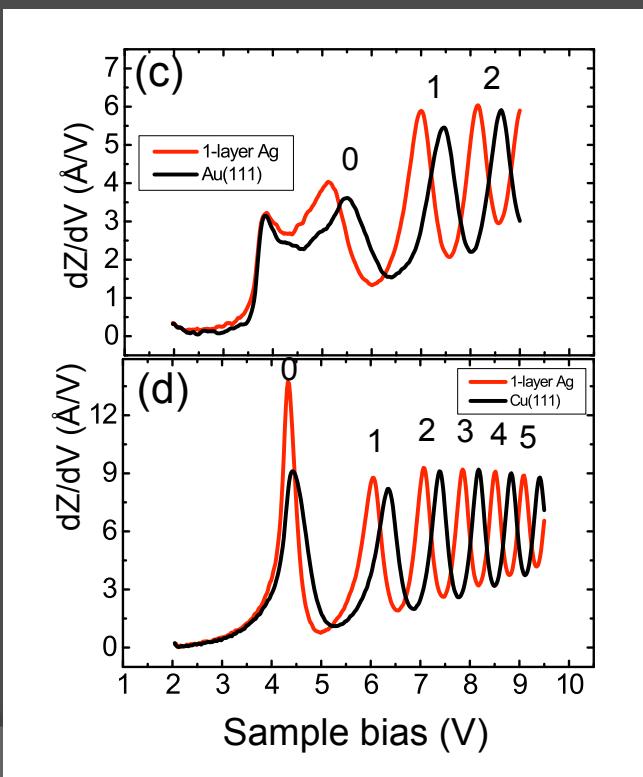
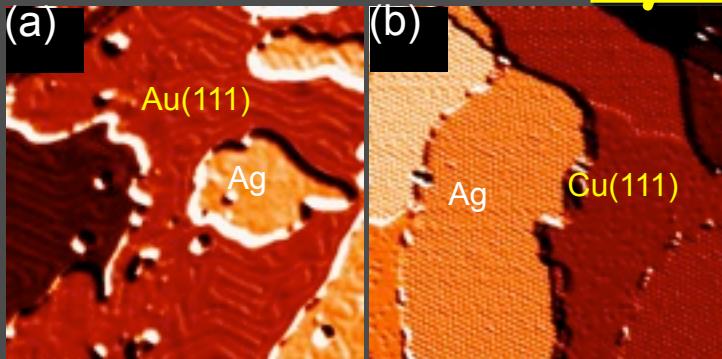
Local probe technique, e.g. STM

# Gundlach oscillation



**Constant energy separation = Work function difference**

# Work function measurements by Gundlach oscillation

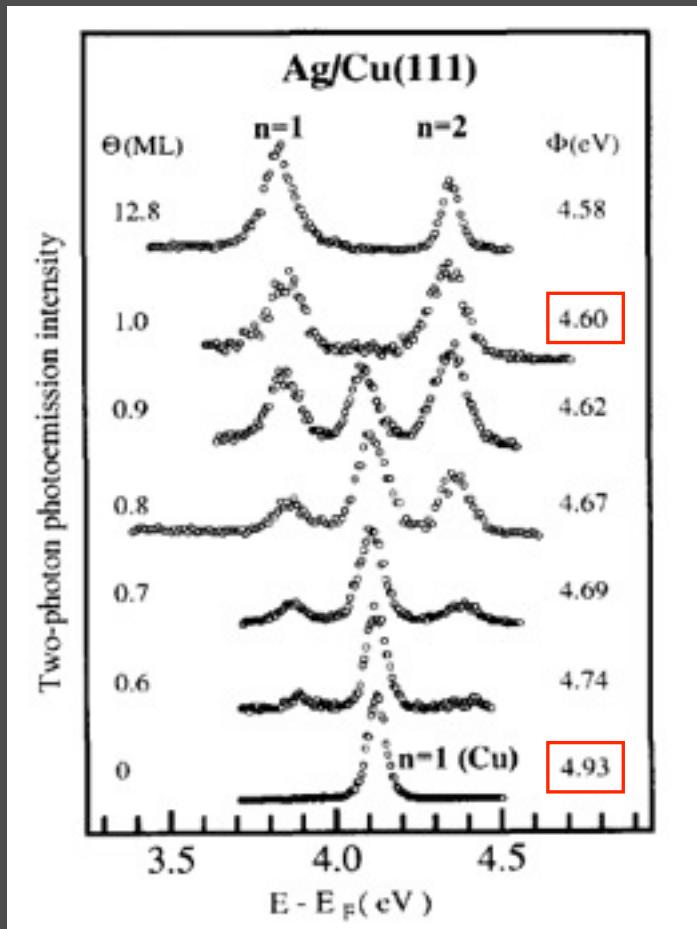


Bulk Materials	$\Phi$ (eV)
Au(111)	5.31
Ag(111)	4.74
Cu(111)	4.98

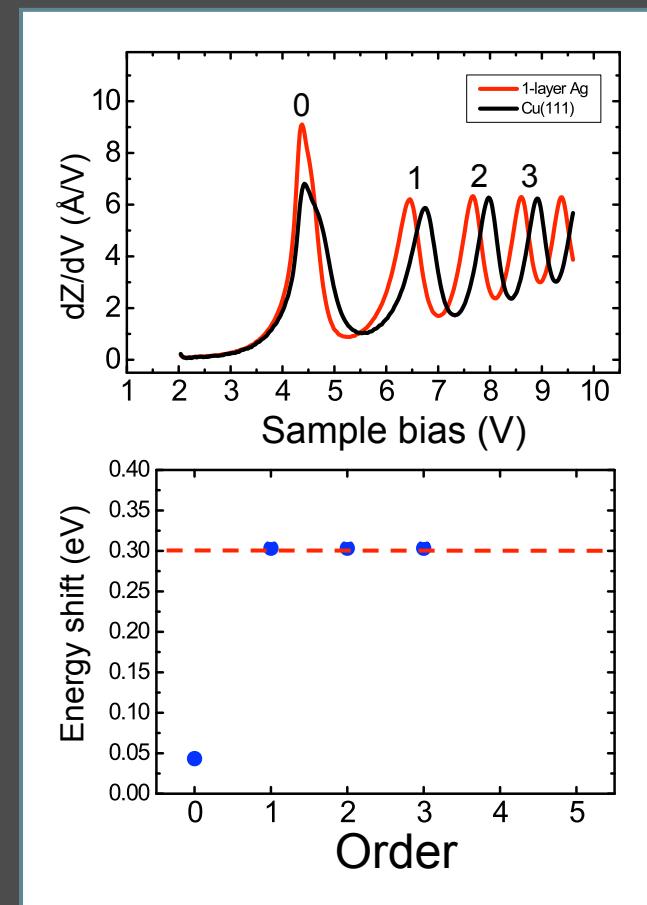
Lin et al., Phys. Rev. Lett. 99, 216103 (2007)

# Comparison with PES measurement

Photoemission (-0.33 eV)

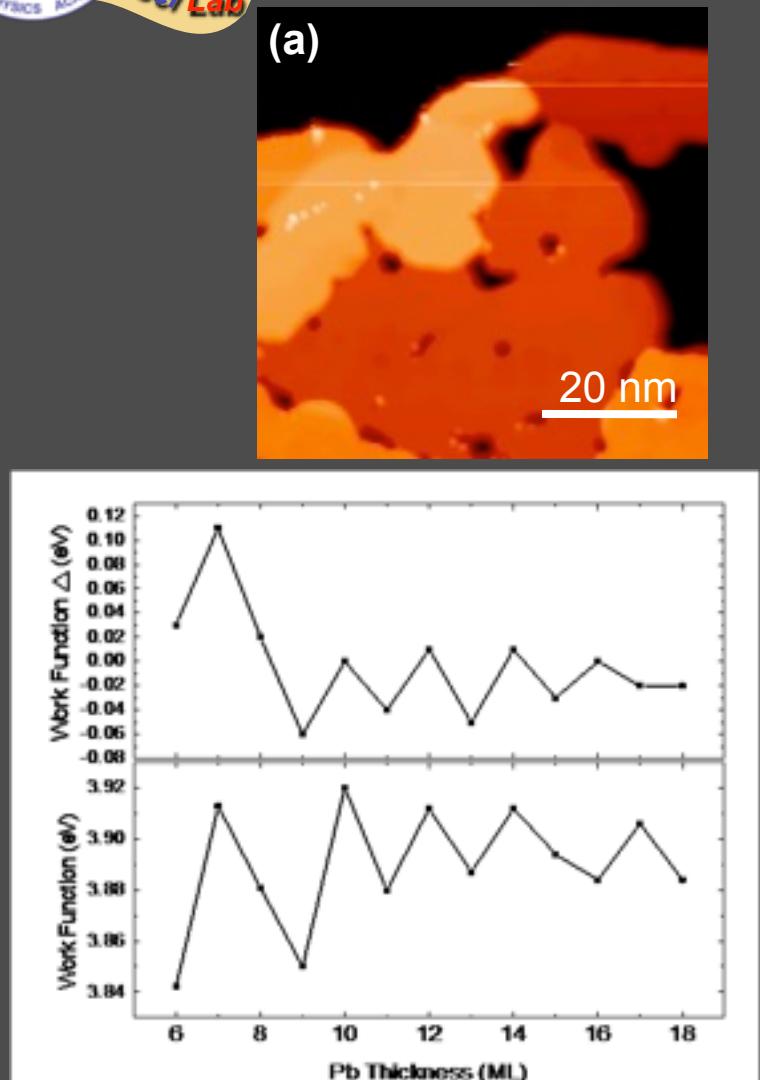


Gundlach oscillation (-0.3 eV)



Wallauer et al., Surf. Sci 331, 731 (1995)

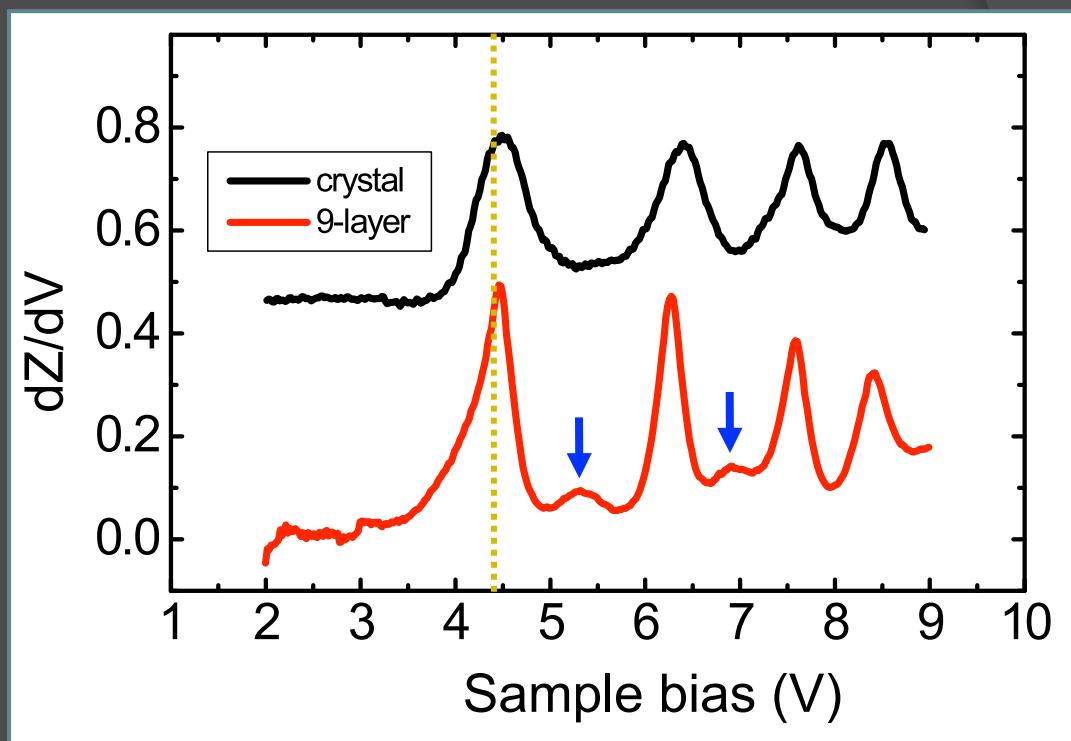
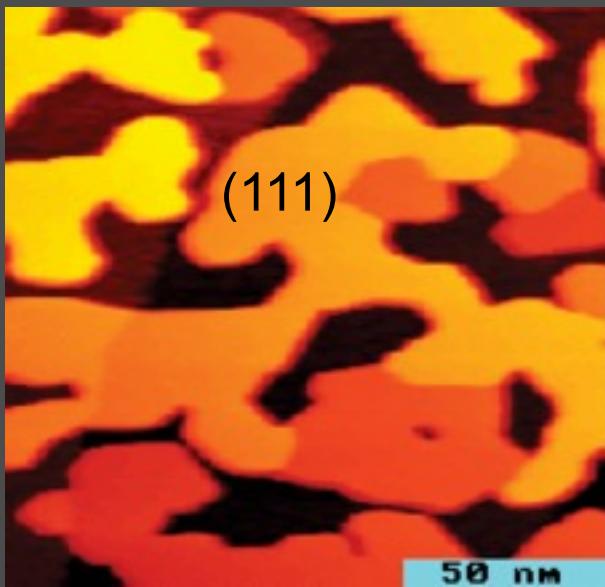
# Work function differences on Pb films



Yu Jia et al., Phys. Rev. B 74, 035433 (2006)

# Transmission Resonance in Ag Films on Si(111)

Ag film on Si(111) at RT

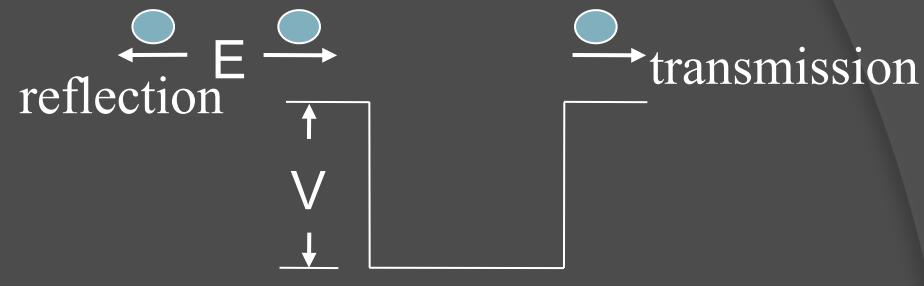
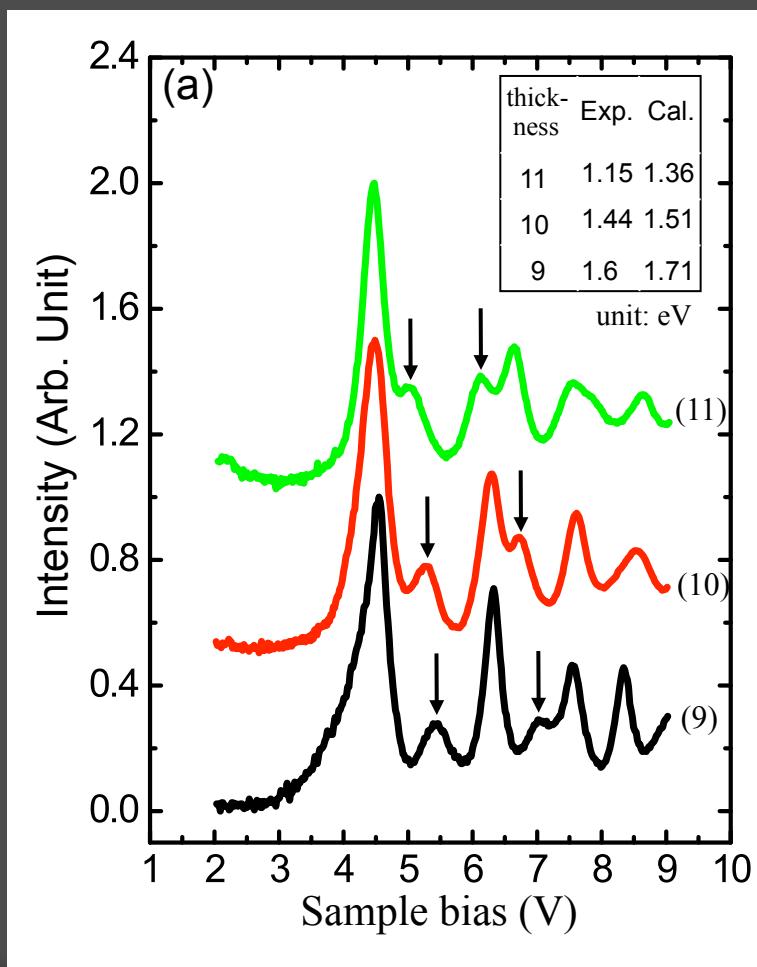


Work function of Ag/Si(111) = 4.41 eV



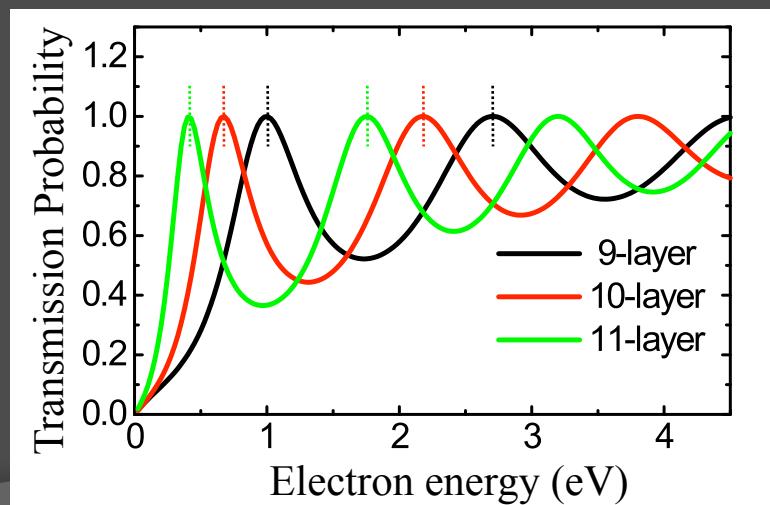
# Quantum Size Effect above Vacuum Level

NanoSciLab



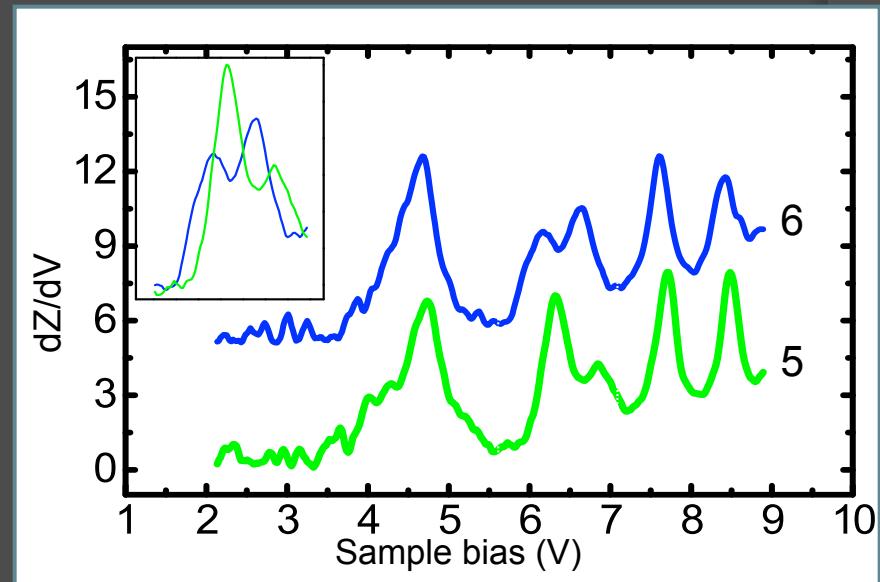
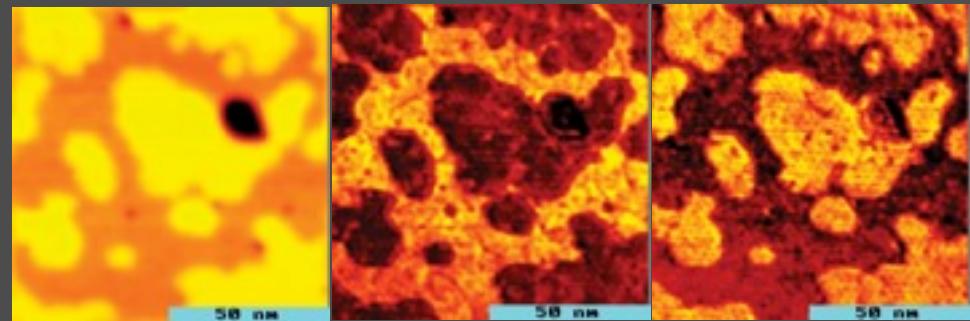
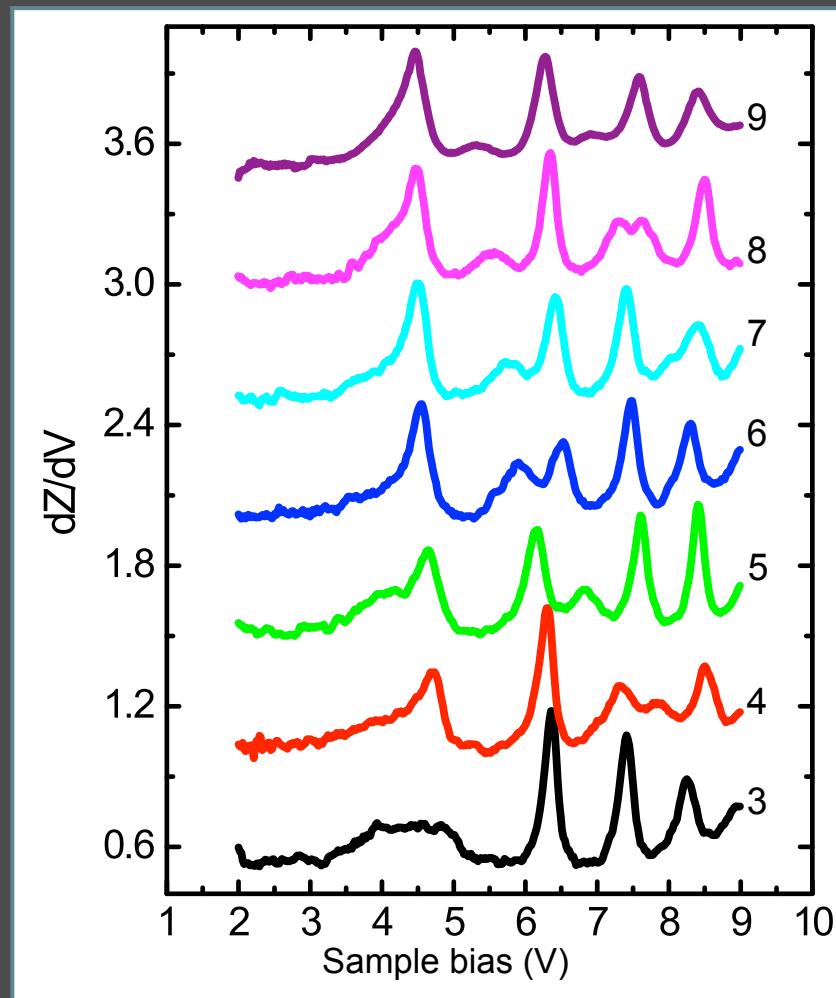
$$\frac{1}{T} = 1 + \frac{1}{4} \frac{V^2}{E(E+V)} \sin^2(kt); R = 1 - T; \frac{\hbar^2 k^2}{2m} = E + V$$

$kt = n\pi \rightarrow T = 1$  transmission resonance



# "Finger print" of film thickness

Low temperature deposition followed annealing to room temperature



## Summary

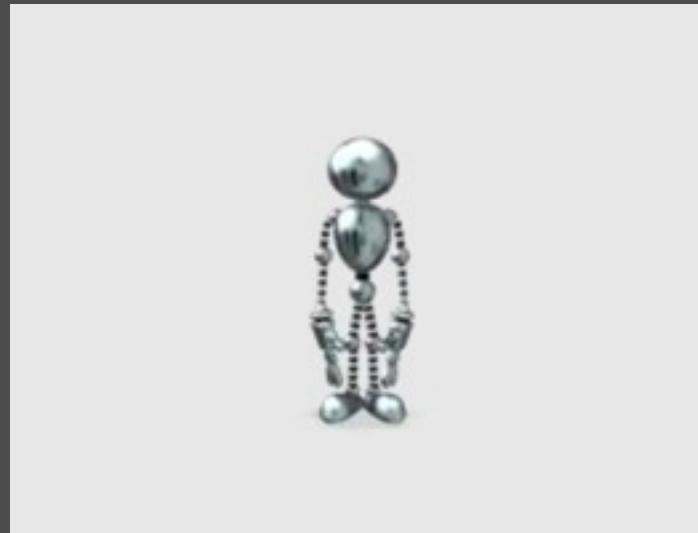
- Quantum well states are measured with STS in the Pb films of varied thickness on the Si(111) surface.
- The lattice mismatch at the interface produces a periodic potential variation, which manifests in a vertical charge oscillation at the surface, and the subtle phenomena of the complementary and alternating contrast reversals through two types of islands with different stacking are observed.
- The QW states in the energy range of 2 - 5 eV above the Fermi level are affected by the image potential, which causes the shrinking in energy separations with the quantum number.

## Summary

- *A general phenomenon of the constant energy shift is observed in high order Gundlach oscillation. The work function of a thin metal film can be measured with the constant energy shift better than 0.02 eV, comparable to the photoemission results.*
- *Quantum transmission resonance can be observed with STS in Ag films on the Si(111) surface. Positions of the transmission resonance measured with STS can serve as finger prints for the Ag films of varied thickness.*

## Acknowledgment

C. L. Lin, S. M. Lu, M.C. Yang, H.Y. Chou,  
W.B. Jian, H.Y. Lin, Y.P. Chiu, and C.M. Wei



**Thank you for your attention**